

transferring the device from the device holding layer onto a second substrate.

[Please add New Claim 16 as follows:]

16. (New) A method for transferring a device as claimed in claim 15, further comprising the step of cleaning the device on the device holding layer after the device is transferred onto the device holding layer.

[Please add New Claim 17 as follows:]

17. (New) A method for transferring a device as claimed in claim 15, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

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[Please add New Claim 18 as follows:]

18. (New) A method for transferring a device as claimed in claim 15, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

[Please add New Claim 19 as follows:]

19. (New) A method for transferring a device as claimed in claim 18, wherein the material is a nitride semiconductor material.

[Please add New Claim 20 as follows:]

20. (New) A method for transferring a device as claimed in claim 19, wherein the nitride semiconductor material is a GaN-based material.

[Please add New Claim 21 as follows:]

21. (New) A method for transferring a device as claimed in claim 15, wherein the first substrate is a sapphire substrate.

[Please add New Claim 22 as follows:]

a' 22. (New) A method for transferring a device as claimed in claim 15, wherein the
cmt. device is a light-emitting device.

[Please add New Claim 23 as follows:]

23. (New) A method for transferring a device as claimed in claim 15, wherein the device holding layer includes a surface with a recessed portion shaped to fit the pointed head portion.

[Please add New Claim 24 as follows:]

24. (New) A method for transferring a device as claimed in claim 15, wherein the device holding layer is a silicone resin layer.

[Please add New Claim 25 as follows:]

25. (New) A method for producing a device holding substrate, comprising the steps of:

preparing a substrate that includes a device having a pointed head portion;

providing an uncured silicone resin layer on a device holding substrate;

coating the device having a pointed head portion with a release agent;

adhering the substrate that includes the device having the pointed head portion to the device holding substrate; and

providing a recessed portion in a surface of the silicone resin layer shaped to fit the pointed head portion.

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cont. [Please add New Claim 26 as follows:]

26. (New) A method for transferring a device, comprising the steps of:
irradiating, selectively, an interface between a first substrate and a device included on the first substrate with an energy beam to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate;

cleaning the device on the device holding layer; and

transferring the device from the device holding layer onto a second substrate.

[Please add New Claim 27 as follows:]

27. A method for transferring a device as claimed in claim 26, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

[Please add New Claim 28 as follows:]

28. A method for transferring a device as claimed in claim 26, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

cont. [Please add New Claim 29 as follows:]

29. A method for transferring a device as claimed in claim 28, wherein the material is a nitride semiconductor material.

[Please add New Claim 30 as follows:]

30. A method for transferring a device as claimed in claim 29, wherein the nitride semiconductor material is a GaN-based material.

[Please add New Claim 31 as follows:]

31. A method for transferring a device as claimed in claim 26, wherein the first substrate is a sapphire substrate.

[Please add New Claim 32 as follows:]

32. A method for transferring a device as claimed in claim 26, wherein the device has one of a pointed head portion and a flat plate-shaped structure.

[Please add New Claim 33 as follows:]

33. A method for transferring a device as claimed in claim 26, wherein the device is a light-emitting device.

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cont. [Please add New Claim 34 as follows:]

34. A method for transferring a device as claimed in claim 26, wherein the device has a pointed head portion, and the device holding layer includes a surface with a recessed portion shaped to fit the pointed head portion.

[Please add New Claim 35 as follows:]

35. A method for transferring a device as claimed in claim 26, wherein the device holding layer is a silicone resin layer.

REMARKS

This response is submitted in reply to the Office Action mailed on October 30, 2002. Claims 1-14 are pending in this application. Claims 8 and 13 were canceled without prejudice. New Claims 15-35 were added. Claims 1, 3, 4 and 9 were rejected under 35 U.S.C. § 102(e); claims 1, 3, 4 and 5 were rejected under 35 U.S.C. § 102(b); claims 2, 5, 6 and 7 were rejected under 35 U.S.C. § 103(a); claims 11, 12 and 14 were rejected under 35 U.S.C. § 103(a); and Claims 8 and 13 were objected to as being dependent upon a rejected base claim.